

ABSTRACT

A single-crystal silicon carbide wafer (31) of the present invention includes boron at a concentration of 1.0×10^{16} atoms/cm³ or less, and has a central region (33) whose basal plane
5 dislocation density is 100/cm² or less on the surface. The central region (33) includes the center of the surface of the single-crystal silicon carbide wafer (31). An area of the central region (33) is one fourth or more of an area of the surface of the single-crystal silicon carbide wafer (31).

FIG. 1